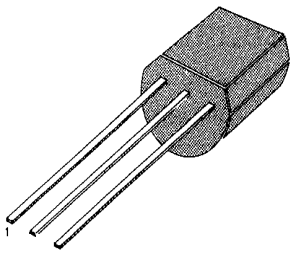
KSP2907A PNP EPITAXIAL SILICON TRANSISTOR

GENERAL PURPOSE TRANSISTOR

- Collector-Emitter Voltage: V_{CEO}= 60V
- Collector Dissipation: P_C(max)=625mW

TO-92



1. Emitter 2. Base 3. Collector

ABSOLUTE MAXIMUM RATINGS (T_A=25℃)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-600	mA
Collector Dissipation	P_C	625	mW
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~150	℃

- Refer to KSP2907 for graphs

ELECTRICAL CHARACTERISTICS (T_A=25℃)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C= -10㎂, I_E=0	-60			V
★Collector Emitter Breakdown Voltage	BV_{CEO}	I_C= -10mA, I_B=0	-40			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E= -10㎂, I_C=0	-5			V
Collector Cut-off Current	I_{CBO}	V_{CB}= -50V, I_E=0			-10	nA
DC Current Gain	h_{FE}	I_C= -0.1mA, V_{CE}= -10V	75			
		I_C= -1mA, V_{CE}= -10V	100			
		I_C= -10mA, V_{CE}= -10V	100			
		★I_C= -150mA, V_{CE}= -10V	100		300	
		★I_C= -500mA, V_{CE}= -10V	50			
★Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C= -150mA, I_B= -15mA			-0.4	V
		I_C= -500mA, I_B= -50mA			-1.6	V
Base Emitter Saturation Voltage	V_{CE} (sat)	I_C= -150mA, I_B= -15mA			-1.3	V
		I_C= -500mA, I_B= -50mA			-2.6	V
Output Capacitance	C_{OB}	V_{CB}= -10V, I_E=0 f=1MHz			8	pF
★Current Gain Bandwidth Product	f_T	I_C= -50mA, V_{CE}= -20V	200			MHz
Turn On Time	t_{ON}	V_{CC}= -30V, I_C= -150mA I_{B1}= -15mA			45	ns
Turn Off Time	t_{OFF}	V_{CC}= -6V, I_C= -150mA I_{B1}=I_{B2}=15mA			100	ns

★Pulse Test: Pulse Width ≤ 300㎲, Duty Cycle ≤ 2%

SAMSUNG ELECTRONICS